

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strike through~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims as noted below.

Listing of the Claims

1. – 10. (CANCELLED)

11. – 18. (CANCELLED)

19. (CURRENTLY AMENDED) A semiconductor package comprising:
a layered stack of two or more semiconductor devices, wherein each semiconductor device layer comprises:
a substrate and a non-device pattern surface formed on one side of the substrate and a ~~non-device~~device pattern surface formed on an opposing side of the substrate;
an insulator bonding layer interposed between the non-device pattern surface of one semiconductor layer and the device pattern surface of an adjacent semiconductor layer;
an electrically insulating epoxy resin protective film bonded to the non-device pattern surface of the lowermost semiconductor layer of the stack; and
a heat radiation layer bonded to the electrically insulating layer protective film, wherein the heat radiation layer has a thickness from about 0.1 μ m to about 1 μ m.

20. (CURRENTLY AMENDED) The semiconductor package of claim 19, wherein the thickness of the heat radiation layer is from about 0.1 μ m to about 0.5 μ m and wherein the ~~epoxy resin is electrically insulating~~ protective film is an epoxy resin.

21. (PREVIOUSLY PRESENTED) The semiconductor package of claim 19, wherein the layered stack is a diced stack.

22. (PREVIOUSLY PRESENTED) The semiconductor package of claim 19, wherein the heat radiation layer comprises Cu, Al or an alloy thereof.

23. (PREVIOUSLY PRESENTED) The semiconductor package of claim 22, wherein the heat radiation layer comprises Cu or an alloy thereof.

24. (PREVIOUSLY PRESENTED) The semiconductor package of claim 22, wherein the heat radiation layer consists essentially of Cu, Al or an alloy thereof.

25. (PREVIOUSLY PRESENTED) The semiconductor package of claim 24, wherein the heat radiation layer consists essentially of Cu or an alloy thereof.

26. (PREVIOUSLY PRESENTED) The semiconductor package of claim 24, wherein the heat radiation layer consists of Cu, Al or an alloy thereof.

27. (CURRENTLY AMENDED) The semiconductor package of claim 19, wherein the insulating layer protective film comprises ~~an epoxy resin or a polyimide resin~~.

28. (CANCELLED)

29. (CANCELLED)

30. (PREVIOUSLY PRESENTED) The semiconductor package of claim 19 further comprising:

a resin sealing layer bonded on the device pattern surface of an uppermost semiconductor device layer.

31. (CURRENTLY AMENDED) The semiconductor package of claim ~~49~~30, wherein the layered stack is diced.

32. (PREVIOUSLY PRESENTED) The semiconductor package of claim 19, wherein each semiconductor device layer comprises an electrode pad formed as part of the device pattern surface of each layer and the electrode pads of successive semiconductor device layers are connected by a via electrode between the electrode pads.

33. (PREVIOUSLY PRESENTED) The semiconductor package of claim 32, wherein the electrode pads and the via electrodes between them comprise Cu or an alloy thereof.

34. (PREVIOUSLY PRESENTED) The semiconductor package of claim 30, wherein the resin sealing layer has a thickness from about 50 μ m to about 90 μ m.

35. (PREVIOUSLY PRESENTED) The semiconductor package of claim 30, wherein the resin sealing layer has a thickness from about 60 μ m to about 80 μ m.

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